

P O S I T I O N I N G

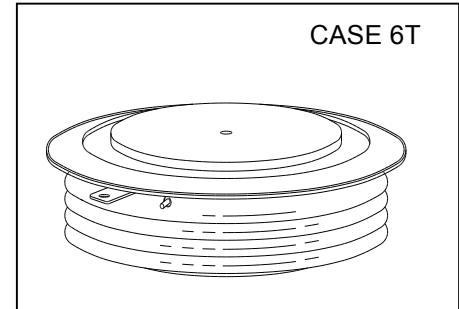
PSTC771 - Power Thyristor

2200 - 2500 V_{DRM}; 2500 A avg

HIGH POWER THYRISTOR FOR INVERTER APPLICATIONS

Features:

- . All Diffused Structure
- . Involute Amplifying Gate Configuration
- . Blocking capability up to 2500 volts
- . Guaranteed Maximum Turn-Off Time
- . High dV/dt Capability
- . Pressure Assembled Device



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V _{RRM} (1)	V _{DRM} (1)	V _{RSM} (1)
PSTC771LB	2200	2200	2300
PSTC771LE	2500	2500	2600

V_{RRM} = Repetitive peak reverse voltage

V_{DRM} = Repetitive peak off state voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I _{RRM} / I _{DRM}	20 mA 100 mA (3)
Critical rate of voltage rise	dV/dt (4)	500 V/μsec

Conducting - on state

Notes:

All ratings are specified for T_j=25 °C unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40 to +125 °C.

(2) 10 msec. max. pulse width

(3) Maximum value for T_j = 125 °C.

(4) Minimum value for linear and exponential waveshape to 80% rated V_{DRM}. Gate open. T_j = 125 °C.

(5) Non-repetitive value.

(6) The value of di/dt is established in accordance with EIA/NIMA Standard RS-397, Section 5-2-2-6. The value defined would be in addition to that obtained from a snubber circuit, comprising a 0.2 μF capacitor and 20 ohms resistance in parallel with the thyristor under test.

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	I _{T(AV)}		2500		A	Sinewave, 180° conduction, T _c =55°C
RMS value of on-state current	I _{TRMS}		3925		A	Nominal value
Peak one cPSTCLe surge (non repetitive) current	I _{TSM}		40000 38000		A A	8.3 msec (60Hz), sinusoidal waveshape, 180° conduction, T _j = 125 °C 10.0 msec (50Hz), sinusoidal waveshape, 180° conduction, T _j = 125 °C
I square t	I ² t		6.8x10 ⁶		A ² s	8.3 msec
Latching current	I _L		1000		mA	V _D = 24 V; R _L = 12 ohms
Holding current	I _H		500		mA	V _D = 24 V; I = 2.5 A
Peak on-state voltage	V _{TM}		2.25		V	I _{TM} = 4000 A; T _j = 125 °C
Critical rate of rise of on-state current (5, 6)	di/dt		800		A/μs	Switching from V _{DRM} ≤ 1000 V, non-repetitive
Critical rate of rise of on-state current (6)	di/dt		400		A/μs	Switching from V _{DRM} ≤ 1000 V

Thyristor

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		200		W	$t_p = 40 \mu s$
Average gate power dissipation	$P_{G(AV)}$		5		W	
Peak gate current	I_{GM}		20		A	
Gate current required to trigger all units	I_{GT}		300 200 125		mA mA mA	$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = -40^\circ C$ $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = +25^\circ C$ $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = +125^\circ C$
Gate voltage required to trigger all units	V_{GT}	0.30	5 4		V V V	$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = -40^\circ C$ $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = 0-125^\circ C$ $V_D = \text{Rated } V_{DRM}; R_L = 1000 \text{ ohms}; T_j = +125^\circ C$
Peak negative voltage	V_{GRM}		20		V	

Dynamic

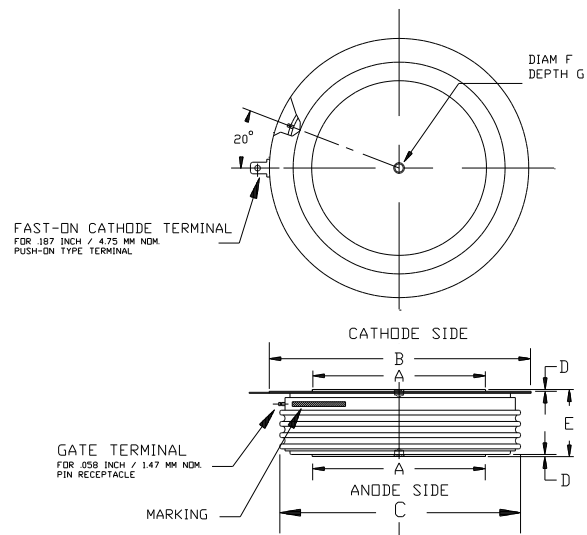
Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t_d		2.0		μs	$I_{TM} = 50 A; V_D = 67\% V_{DRM}$ Gate pulse: $V_G = 30 V; R_G = 10 \text{ ohms};$ $t_r = 0.1 \mu s; t_b = 20 \mu s$
Turn-off time (with $V_R = -5 V$)	t_q		80		μs	$I_{TM} > 2000 A; di/dt = 25 A/\mu s;$ $V_R \geq -5 V; \text{Re-applied } dV/dt = 400$ $V/\mu s \text{ linear to } 67\% V_{DRM};$ $T_j = 125^\circ C; \text{Duty cPSTC} \geq 0.01\%$
Reverse recovery current	I_{rr}		450		A	$I_{TM} > 2000 A; di/dt = 50 A/\mu s;$ $V_R \geq -50 V; T_j = 125^\circ C$

THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+125		$^\circ C$	
Storage temperature	T_{stg}	-40	+150		$^\circ C$	
Thermal resistance - junction to case	$R_{\theta(j-c)}$		0.012		$^\circ C/W$	Double sided cooled
Thermal resistance - case to sink	$R_{\theta(c-s)}$		0.001		$^\circ C/W$	Double sided cooled *
Mounting force	P	8000 35.5	10000 44.4		lb. kN	
Weight	W			3.5 1.60	Lb. Kg.	

* Mounting surfaces smooth, flat and greased

Note : for case outline and dimensions, see case outline drawing in page 3 of this Technical Data



CASE 5T
NOMINAL OUTLINE DIMENSIONS

DIMENSIONS	INCH	MM
DIAM. A	2.88	73.2
DIAM. B	4.36	110.7
DIAM. C	3.95	100.3
D	.030	.76
E	1.400 / 1.440	35.56 / 36.58
F	.140	3.56
G	.080	2.03

STRIKE DISTANCE = 1.04 inch / 26.4 mm MIN.
CREEPAGE DISTANCE = 1.64 inch / 41.6 mm MIN.

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